

21  
that said specific WIW or WID process effect can be achieved on said wafer by selectively moving said wafer frictionally one of said plurality of regions, each of said plurality of regions having a respective underlying layer adapted to achieve said specific WIW or WID process effect.

---

22  
21. (Amended) A process specific polishing pad having a plurality of regions configured to implement different polishing hardness on the surface of a wafer, the process specific polishing pad comprising:

a polishing pad having an overlying layer, said overlying layer being uniform and homogenous across a polishing surface of said overlying layer, said polishing surface adapted to frictionally contact a wafer as said wafer is polished in said wafer polishing machine; and

said polishing surface having a plurality of regions, each of said plurality of regions configured to achieve a specific WIW or WID effect by using a respective underlying layer in conjunction with the uniform and homogenous overlying layer, wherein the respective underlying layer of each of said plurality of regions is adapted to achieve said specific WIW or WID effect.

---